风光欣技术资料

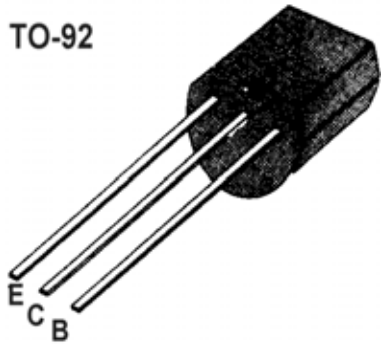
A720

—PNP silicon —

■■**APPLICATION**：General Purpose Applications.

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-500	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃



■■**ELECTRICAL CHARACTERISTICS**（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE1}	85		340		V_{CE}= -10V，Ic= -150mA
	h_{FE2}	40				V_{CE}= -10V，Ic= -500mA
Collector Cut-off Current	I_{CBO}			-0.1	μA	V_{CB}= -20V，I_E=0
Emitter Cut-off Current	I_{EBO}			-0.1	μA	V_{EB}= -3V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	-60			V	Ic= -0.01mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-50			V	Ic= -10mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	I_E= -0.01mA，Ic=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.35	-0.6	V	Ic= -300mA，I_B= -30mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-1.1	-1.5	V	Ic= -300mA，I_B= -30mA
Gain bandwidth product	f_T	100	200		MHz	Ic= -50mA，V_{CE}= -10V，f = 200 MHz
Common Base Output Capacitance	Cob		6	15	pF	V_{CB}= -10V，I_E=0，f = 1 MHz

■■h_{FE} **Classification**

Classification	Q	R	S
h_{FE}	85~170	120~240	170~340